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an inner lead frame made of a sheet metal, one end of the inner lead frame being connected to the main electrode so as to cover at least a part of the Schottky diode, a second end of the inner lead frame being connected to a package lead.

24. (Amended) A semiconductor device comprising:

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a transistor chip having a first main electrode and a gate electrode on an upper surface of the transistor chip, a second main electrode on a bottom surface of the transistor chip, a transistor region including a transistor, operation of which is controlled by the first main electrode, the gate electrode, and the second main electrode, and a diode region in which a Schottky diode is connected in parallel to the transistor;

a package base to which the second main electrode of the transistor chip is joined and connected;

an inner lead frame made of a sheet metal, one end of the inner lead frame being connected to the main electrode on at least a part of the diode region, a second end of the inner lead frame being connected to a package lead.

REMARKS

Favorable reconsideration of this application is respectfully requested.

Claims 8-26 are pending in this application. Claims 8-20 are allowed. Claims 21-23 and 25 were rejected under 35 U.S.C. § 112, first paragraph. Claims 21-26 were rejected under 35 U.S.C. § 112, second paragraph. Claims 24 and 26 were rejected under 35 U.S.C. § 103(a) as unpatentable over U.S. patent 6,144,093 to Davis et al. (herein "Davis") in view of U.S. patent 5,925,926 to Watanabe.

Initially, applicants gratefully acknowledge the early indication of the allowance of claims 8-20.